Vishay Semiconductors



Phase Control Thyristors (Hockey PUK Version), 960 A



### E-PUK (TO-200AB)

PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub> 960 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 600 V						
V <sub>TM</sub>	1.58 V						
I <sub>GT</sub>	100 mA						
TJ	-40 °C to +150 °C						
Package	E-PUK (TO-200AB)						
Circuit configuration	Single SCR						

### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)
- Extended temperature range
- Low profile hockey PUK to increase current-carrying capability
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		960	А				
I <sub>T(AV)</sub>	T <sub>hs</sub>	80	°C				
1		2220	А				
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C				
1	50 Hz	12 500	٨				
ITSM	60 Hz	13 000	A				
l <sup>2</sup> t	50 Hz	782	1.42-				
1-1	60 Hz	713	kA <sup>2</sup> s				
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V				
t <sub>q</sub>	Typical	100	μs				
TJ		-40 to 150	°C				

## **ELECTRICAL SPECIFICATIONS**

VOLTAGE RA	ATINGS				
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I <sub>DRM</sub> /I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA	
VS-ST380CHC	04	400	500	100	
06		600	700	100	



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current		, 180° conduction, h		vave	960 (440)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	80 (110)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	2220	
		t = 10 ms	No voltage		12 500	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		13 000	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		10 500	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	11 000	
<b>.</b>	l <sup>2</sup> t	t = 10 ms	No voltage reapplied 100 % V <sub>BBM</sub>		782	
		t = 8.3 ms			713	
Maximum I <sup>2</sup> t for fusing		t = 10 ms			553	
		t = 8.3 ms	reapplied		505	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	reapplied	7820	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.85	v
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), T <sub>J</sub> = T <sub>J</sub> maxin	num	0.88	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)})$	0.24	mΩ		
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 2900 A	$A, T_J = T_J maxim$	um, t <sub>p</sub> = 10 ms sine pulse	1.58	V
Maximum holding current	Ι <sub>Η</sub>	т об ос	anada ayanki 4		600	
Typical latching current	١L	$I_{\rm J} = 25^{-1}$ C,	anoue supply 1	2 V resistive load	1000	mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \le 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs				
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/µs $V_d$ = 0.67 % $V_{DRM}$ , $T_J$ = 25 °C	1.0					
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	100	μs				

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs				
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA				



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TRIGGERING						
PARAMETER	SYMBOL	TES	VALUES			
PARAMEIER	STMBUL		TYP.	MAX.		
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	А
Maximum peak positive gate voltage	+ V <sub>GM</sub>		t < 5 mg	2	:0	v
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum,	5.0		v	
		T <sub>J</sub> = -40 °C		200	-	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/ current/voltage are the lowest	100	200	mA
		T <sub>J</sub> = 150 °C		40	-	
		T <sub>J</sub> = -40 °C	value which will trigger all units	2.5	-	
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 150 °C		1.0	-	
DC gate current not to trigger	I <sub>GD</sub>	T T. movimum	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL TEST CONDITIONS		VALUES	UNITS			
Maximum operating junction temperature range	TJ		-40 to 150	°C			
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150	C			
Maximum thermal registance, junction to bestaink	D	DC operation single side cooled	0.09				
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.04	K/W			
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled	0.02	10/00			
		DC operation double side cooled	0.01				
Mounting force, ± 10 %			9800 (1000)	N (kg)			
Approximate weight			83	g			
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-2	200AB)			

CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION	TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.010	0.011	0.007	0.007				
120°	0.012	0.012	0.012	0.013				
90°	0.015	0.015	0.016	0.017	$T_J = T_J maximum$	K/W		
60°	0.022	0.022	0.023	0.023				
30°	0.036	0.036	0.036	0.037				

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

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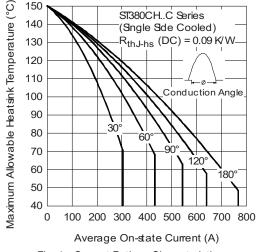
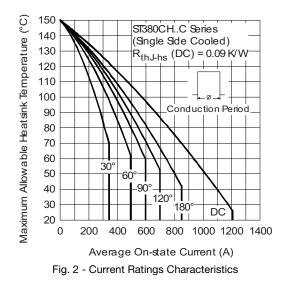
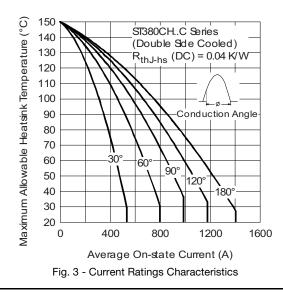
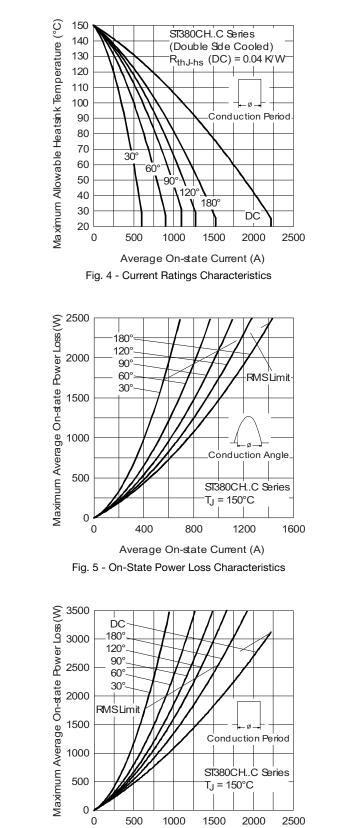


Fig. 1 - Current Ratings Characteristics





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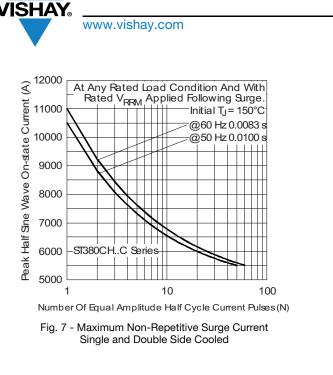
Average On-state Current (A) Fig. 6 - On-State Power Loss Characteristics

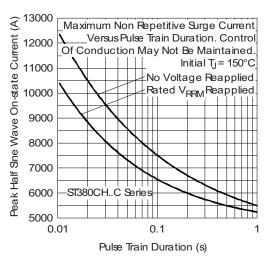
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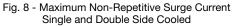
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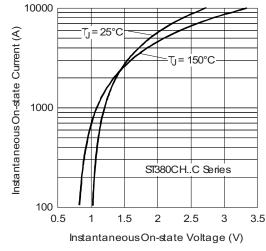
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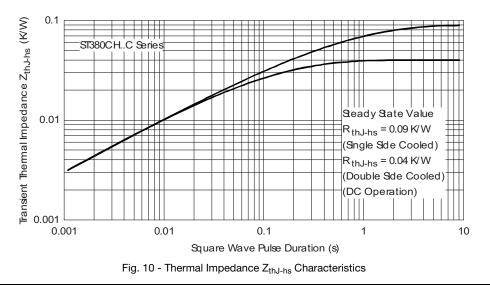












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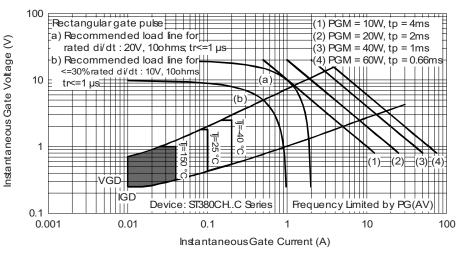


Fig. 11 - Gate Characteristics

## **ORDERING INFORMATION TABLE**

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Device code	VS-	ST	38	0	СН	06	С	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -	Visł	nay Sen	niconduo	ctors pro	oduct				
	2 -	Thy	ristor							
	3 -	Ess	ential pa	art numl	ber					
	4 -	0 =	convert	er grade	9					
	5 -	СН	CH = ceramic PUK, high temperature							
	6 -	Volt	Voltage code x 100 = V <sub>RRM</sub> (see Voltage Ratings table)							
	7 -	C =	C = PUK case E-PUK (TO-200AB)							
	8 -	0 =	eyelet t	erminals	s (gate a	ind auxi	iliary ca	thode u	nsoldere	ed leads
		1 =	fast-on	terminal	ls (gate	and aux	kiliary ca	athode (	unsoldei	red lead
		2 =	eyelet te	erminals	s (gate a	ind auxi	liary cat	thode s	oldered	leads)
		3 =	fast-on	terminal	s (gate	and aux	kiliary ca	athode s	soldered	l leads)
	9 -	Crit	ical dV/o	dt: • No	ne = 50	0 V/µs (	standar	d selec	tion)	
				• L =	= 1000 V	//µs (sp	ecial se	lection)		

LINKS TO RELATED DOCUMENTS					
Dimensions	http://www.vishay.com/doc?95075				

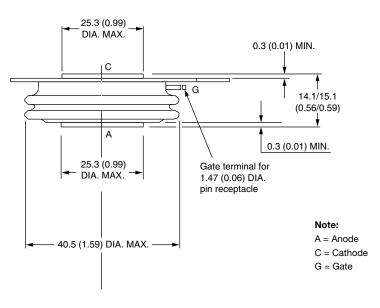
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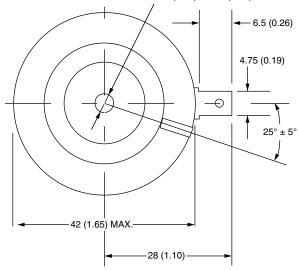
# E-PUK (TO-200AB)

#### **DIMENSIONS** in millimeters (inches)

Anode to gate Creepage distance: 11.18 (0.44) minimum Strike distance: 7.62 (0.30) minimum



2 holes 3.56 (0.14) x 1.83 (0.07) minimum deep



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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